The 22<sup>nd</sup> Korean Conference on Semiconductors (KCS 2015)

제22회 한국반도체학술대회

2015년 2월 10일(화)-12일(목), 인천 송도컨벤시아

## G. Device & Process Modeling, Simulation and Reliability 분과

Room C 1F / 106호

2015년 2월 12일(목) 14:50-16:20

[TC3-G] RF and Terahertz Devices

좌장: 이정수 (포항공과대학교), 이재규 (삼성전자)

TC3-G-1	14:50-15:05	Large-Signal Simulation of Plasma Instability in 2-Dimensional Electron
		Gas
		Sung-Min Hong and Jae-Hyung Jang
		School of Information and Communications, Gwangju Institute of Science
		and Technology
TC3-G-2	15:05-15:20	Voltage-Dependent SPICE Modeling for Gate-Drain Overlap Capacitance
		in RF MOSFETs
		Sangjun Lee and Seonghearn Lee
		Department of Electronic Engineering, Hankuk University of Foreign Studies
TC3-G-3	15:20-15:35	Physical Modeling and Analysis for Performance Enhancement of
		Terahertz Wave Detector based on Silicon Field-Effect Transistor
		Kwan Sung Kim, Min Woo Ryu, Jeong Seop Lee, and Kyung Rok Kim
		School of Electrical and Computer Engineering, UNIST
TC3-G-4	15:35-15:50	Intrinsic Output Equivalent Circuit Modeling for RF MOSFETs
		Seoyoung Hong and Seonghearn Lee
		Department of Electronic Engineering, Hankuk University of Foreign Studies
TC3-G-5	15:50-16:05	Amplification of Electromagnetic Waves in InAlN/AlN/GaN Grating
		Structures
		Cho Hee Lee, Ji Hyun Hwang, Jae-Hyung Jang, and Sung-Min Hong
		School of Information and Communications, Gwangju Institute of Science
		and Technology
TC3-G-6	16:05-16:20	The DRC-based Check Tool for New ESD Failure Mechanism
		Youngchul.Kim, Euiyoun.Hong, Dongsin.Kim, Hyunkwang.Jeong,
		Wanchul.Kong, Kihyun.Kim, and Sungbum.Park
		Lib& DT team, Corporate Engineering, Magnachip Semiconductor